09-13-04

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Express Mail No. EL963273053US
ELM/001 Cont. 14

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| Applicant | : | Glenn J. Leedy | |
| Application No. | : | 10/766,557 | Confirmation No. : 3092 |
| Filed | : | January 27, 2004 | |
| For | : | METHODS FOR MASKLESS LITHOGRAPHY | |
| Examiner | : | Not yet assigned | |
| Group Art Unit | : | 2812 | |

New York, New York 10020
September 10, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicants wish to call the attention of the Examiner to the following documents:

U.S. Patent Documents

| | | |
|---|---|---|
| Shibata | 4,500,905 | 02/19/1985 |
| Wang, et al. | 4,892,753 | 01/09/1990 |
| Kato, et al. | 4,939,568 | 07/03/1990 |
| Wang, et al. | 5,000,113 | 03/19/1991 |
| Linglain, et al. | 5,240,458 | 08/31/1993 |
| Bantien | 5,259,247 | 11/09/1993 |
| Fujii, et al. | RE 34,893 | 04/04/1995 |
| Wang, et al. | RE 36,623 | 03/21/2000 |
| Brix, et al. | 6,087,284 | 07/11/2000 |
| Momohara | 6,518,073 | 02/11/2003 |

Foreign Patent Documents

| | | |
|---|---|---|
| Japan | 04-196263 | 07/1992 |

## Other Documents

Aboaf, J.A., "Stresses in $SiO_2$ Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate - Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).

Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970).

Bailey, R., "Glass for Solid-State Devices: Glass film has low intrinsic compressive stress for isolating active layers of magnetic-bubble and other solid-state devices," NASA Tech Brief (1982).

"Partitioning Function and Packaging of Integrated Circuits for Physical Security of Data," IBM Technical Disclosure Bulletin, IBM Corp.; 32(1): 46-49 (June 1989).

Hsieh, et al., "Directional Deposition of Dielectric Silicon Oxide by Plasma Enhanced TEOS Process," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, pp. 411-415 (1989).

Tessier, et al., "An Overview of Dielectric Materials for Multichip Modules," SPE, Electrical & Electronic Div.; (6): 260-269 (1991).

Treichel, et al., "Planarized Low-Stress Oxide/Nitride Passivation for ULSI Devices," J. Phys IV, Colloq. (France), 1 (C2): 839-846 (1991).

Krishnamoorthy, et al., "3-D Integration of MQW Modulators Over Active Submicron CMOS Circuits: 375 Mb/s Transimpedance Receiver -Transmitter Circuit," IEEE Photonics Technology Letters, 2(11): 1288-1290 (November 1995).

Tielert, et al., "Benefits of Vertically Stacked Integrated Circuits for Sequential Logic," IEEE, XP-000704550, 121-124 (December 5, 1996).

"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short

Working Distances, Enable Operation in Air," NASA Tech Briefs, 39-40 (1998).

Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

Copies of the aforementioned documents, which are listed on the accompanying Form PTO-1449 (submitted in duplicate), are enclosed herewith.

It is respectfully requested that these documents be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is being submitted more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97(b)(3), submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Supplemental Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this statement is transmitted herewith.

An early and favorable action is respectfully requested.

Respectfully submitted,

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New York, New York 10020
Tel.: (212) 596-9000

| FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. ELM/001 Cont. 14 | APPLN. NO. 10/766,557 |
|---|---|---|
| SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT | APPLICANTS Glenn J. Leedy | CONF. NO. 3092 |
| | FILING DATE January 27, 2004 | GROUP ART UNIT 2812 |



**U.S. PATENT DOCUMENTS**

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|---|---|---|---|---|---|---|
| | 4,500,905 | 02/19/1985 | Shibata | 357 | 68 | |
| | 4,939,568 | 07/03/1990 | Kato, et al. | 357 | 75 | |
| | 4,892,753 | 01/09/1990 | Wang, et al. | 427 | 579 | |
| | 5,000,113 | 03/19/1991 | Wang, et al. | 118 | 723 | |
| | 5,240,458 | 08/31/1993 | Linglain, et al. | 464 | 63 | |
| | 5,259,247 | 11/09/1993 | Bantien | 73 | 718 | |
| | RE 34,893 | 04/04/1995 | Fujii, et al. | 257 | 419 | |
| | RE 36,623 | 03/21/2000 | Wang, et al. | 427 | 579 | |
| | 6,087,284 | 07/11/2000 | Brix, et al. | 501 | 69 | |
| | 6,518,073 | 02/11/2003 | Momohara | 438 | 4 | 12/10/2001 |

**FOREIGN PATENT DOCUMENTS**

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
|---|---|---|---|---|---|---|---|
| | | | | | | YES | NO |
| | 04-196,263 | 07/1992 | Japan | | | | |

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

| EXAMINER INITIAL | |
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| | Aboaf, J.A., "Stresses in $SiO_2$ Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate – Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969). |
| | Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970). |
| | Bailey, R., "Glass for Solid-State Devices: Glass film has low intrinsic compressive stress for isolating active layers of magnetic-bubble and other solid-state devices," NASA Tech Brief (1982). |
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**EXAMINER** **DATE CONSIDERED**

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.**

| FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. ELM/001 Cont. 14 | APPLN. NO. 10/766,557 |
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EXPRESS MAIL CERTIFICATION

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Date of Deposit: September 10, 2004

I hereby certify that this certification and the following papers and fees:

1. Supplemental Information Disclosure Statement (in duplicate);

2. Form PTO-1449 (in duplicate);

3. Copies of twenty-two (22) cited references; and

4. Return postcard

are being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 37 C.F.R. § 1.10 on the date indicated above and are addressed to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Name: Claire J. Saintil-van Goodman